

# 10L80 DO-201AD

Trench MOS Barrier Schottky Rectifier

**DO-201AD**

**10L80**



Cathode → Anode

## Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

## Applications

- DC/DC Converters
- AC/DC Adaptors

## Maximum ratings and electrical characteristics (TJ = 25°C unless otherwise noted)

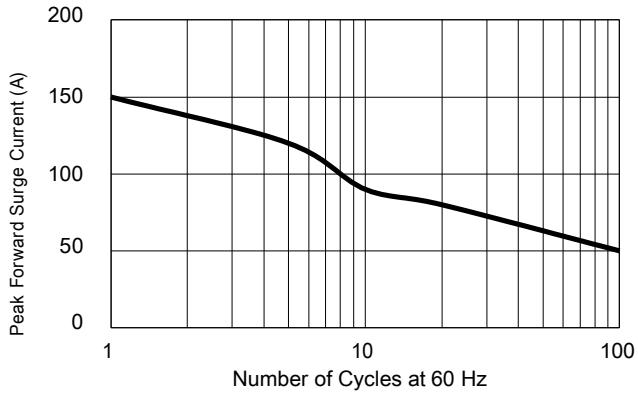
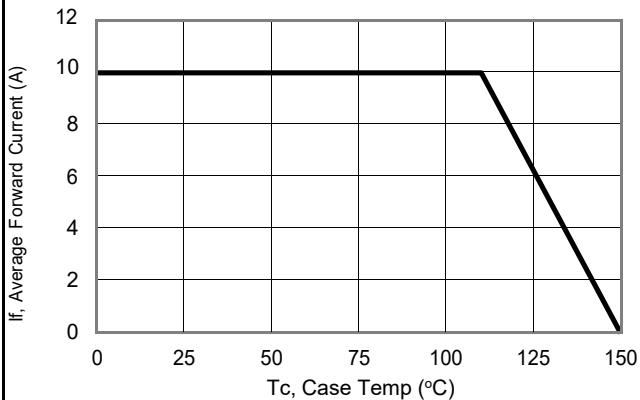
Parameter	Symbol	Limit	Unit
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	80	V
Maximum average forward rectified current	I <sub>F(AV)</sub>	10	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	200	A
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	-40 to +150	°C
Typical thermal resistance per diode (Mounted on FR-4 PCB)	R <sub>θJC</sub>	22	°C/W
Instantaneous forward voltage I <sub>F</sub> =2A TJ=25°C	V <sub>F(1)</sub>	TYP.	MAX.
		0.42	-
		0.37	-
		0.60	0.64
		0.56	-
Instantaneous reverse current per diode at rated reverse voltage	I <sub>R(2)</sub>	-	10
		-	10
			uA
			mA

Notes:

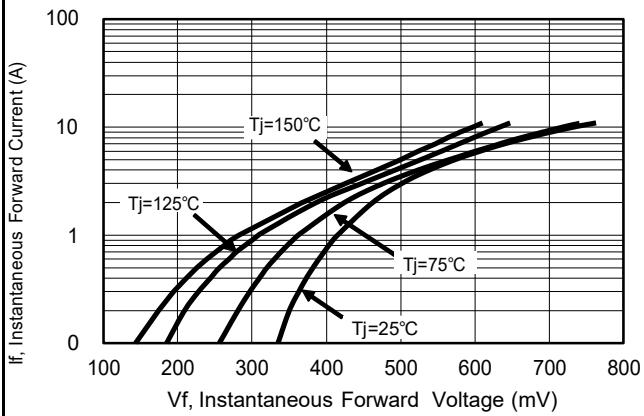
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

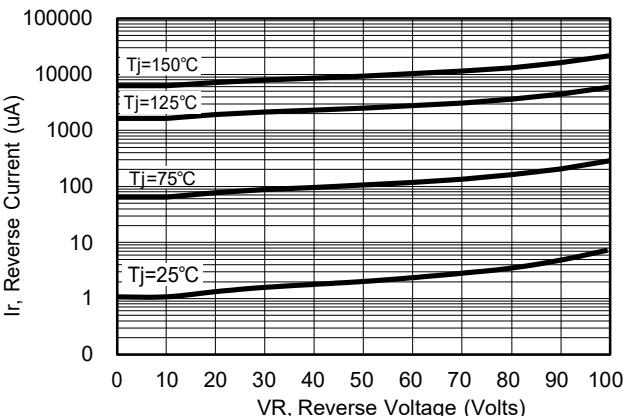
## RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



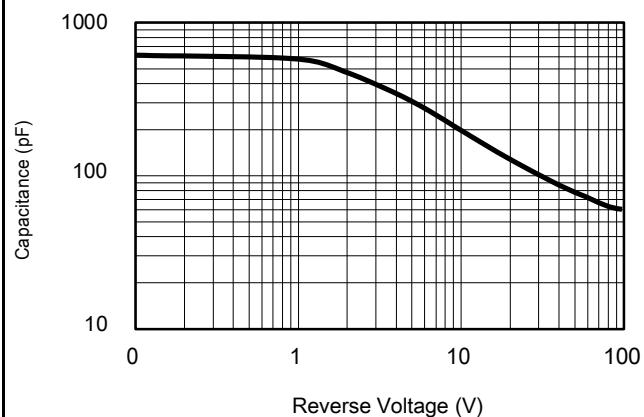
**Current Derating, Case**



**Maximum Repetitive Surge Current**



**Typical Forward Voltage**

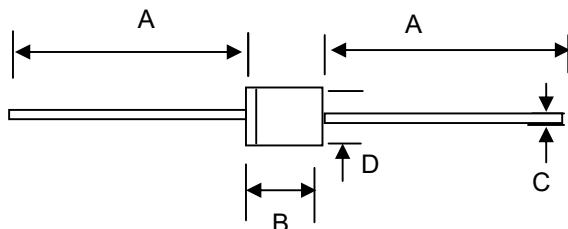


**Typical Reverse Current**

**Typical Junction Capacitance**

## PACKAGE OUTLINE

### DO-201AD



DO-201AD		
Dim.	Min.	Max.
A	25.4	-
B	7.3	9.5
C	1.2	1.3
D	4.8	5.3

All Dimensions in mm